



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Toshimitsu Taniguchi et al.
Serial No. : 09/891,580
Filed : June 26, 2001
Title : SEMICONDUCTOR DEVICE MANUFACTURING METHOD

Art Unit : 2825
Examiner : Igwe U. Anya

Commissioner for Patents
Washington, D.C. 20231

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TECHNOLOGY CENTER 2825

RESPONSE

In response to the action mailed August 6, 2002, please amend the application as follows:

In the claims:

Please amend claims 1, 4, and 7 to 11 as follows (unamended claims are shown in small, bold type-face for ease of reference):

Sub B1
On
-- 1. (Amended) A semiconductor device manufacturing method comprising:
providing a substrate having a first formation area and a second formation area;
forming an oxide film on the first and the second formation areas;
forming an oxidation resistance film on the oxide film;
masking the second formation area by disposing a photoresist on the oxidation resistance
film above the second formation area;
removing the oxidation resistant film above the first formation area;
removing the photoresist above the second formation area;
removing the oxide film above the first formation area while using the oxidation resistant
film above the second formation area as a mask; .
forming a first oxide film on the first formation area;

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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